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LM101AQML Operational Amplifiers General Description

The LM101A is a general purpose operational amplifier which features improved performance over industry standards such as the LM709. Advanced processing techniques make possible an order of magnitude reduction in input currents, and a redesign of the biasing circuitry reduces the temperature drift of input current. Improved specifications include:

- Offset voltage 3 mV maximum over temperature
- Input current 100 nA maximum over temperature
- Offset current 20 nA maximum over temperature
- Guaranteed drift characteristics
- Offsets guaranteed over entire common mode and supply voltage ranges
- Slew rate of 10V/µs as a summing amplifier
- This amplifier offers many features which make its application nearly foolproof: overload protection on the input and output, no latch-up when the common mode range is exceeded, and freedom from oscillations and compensation with a single 30 pF capacitor. It has advantages over internally compensated amplifiers in that the frequency compensation can be tailored to the particular application. For example, in low frequency circuits it can be

overcompensated for increased stability margin. Or the compensation can be optimized to give more than a factor of ten improvement in high frequency performance for most applications.

In addition, the device provides better accuracy and lower noise in high impedance circuitry. The low input currents also make it particularly well suited for long interval integrators or timers, sample and hold circuits and low frequency waveform generators. Further, replacing circuits where matched transistor pairs buffer the inputs of conventional IC op amps, it can give lower offset voltage and a drift at a lower cost.

Features

- Available with radiation guarantee
- Offset voltage 3 mV maximum over temperature
- Input current 100 nA maximum over temperature
- Offset current 20 nA maximum over temperature
- Guaranteed drift characteristics
- Offsets guaranteed over entire common mode and supply voltage ranges
- Slew rate of 10 V/µS as a summing amplifier

Ordering Information

•			
NS Part Number	SMD Part Number	NS Package Number	Package Description
LM101AH/883		H08C	8LD Metal Can
LM101AJ/883		J08A	8LD CERDIP
LM101AW/883		W10A	10LD CERPACK
LM101AH-QMLV	5962-9951501VGA	H08C	8LD Metal Can
LM101AHLQMLV	5962L9951501VGA	H08C	8LD Metal Can
	50k rd(Si)		
LM101AHRQMLV	5962R9951501VGA	H08C	8LD Metal Can
	100k rd(Si)		
LM101AJLQMLV	5962L9951501VPA	J08A	8LD CERDIP
	50k rd(Si)		
LM101AJ-QMLV	5962-9951501VPA	J08A	8LD CERDIP
LM101AW-QMLV	5962-9951501VHA	W10A	10LD CERPACK
LM101AWLQMLV	5962L9951501VHA	W10A	10LD CERPACK
	50k rd(Si)		

Schematic (Note 11)





Note 1: Feedforward compensation can be used to make a fast full wave rectifier without a filter.

Absolute Maximum Ratings (Note 2)

Supply Voltage Differential Input Voltage Input Voltage (Note 3) Output Short Circuit Duration Operating Ambient Temp. Range	$\pm 22V$ $\pm 30V$ $\pm 15V$ Continuous $-55^{\circ}C \leq T_{A} \leq +125^{\circ}C$
T _J Max	150°C
Power Dissipation at $T_A = 25^{\circ}C$ (Note 4)	
H-Package	
(Still Air)	750 mW
(500 LF / Min Air Flow)	1200 mW
J-Package	
(Still Air)	1000 mW
(500 LF / Min Air Flow)	1500 mW
W-Package	
(Still Air)	500mW
(500 LF / Min Air Flow)	800mW
Thermal Resistance	
θ_{JA}	
H-Package	
(Still Air)	165°C/W
(500 LF / Min Air Flow)	89°C/W
J-Package	
(Still Air)	128°C/W
(500 LF / Min Air Flow)	75°C/W
W-Package	
(Still Air)	233°C/W
(500 LF / Min Air Flow)	155°C/W
θ _{JC} (Typical)	
H-Package	39°C/W
J-Package	26°C/W
W-Package	26°C/W
Storage Temperature Range	$-65^{\circ}C \le T_{A} \le +150^{\circ}C$
Lead Temperature (Soldering, 10 sec.)	300°C
ESD Tolerance (Note 5)	3000V

Quality Conformance Inspection Mil-Std-883, Method 5005 - Group A

(°C)		
5		
25		

LM101AQML

Subgroup	Description	Temp (°C)
1	Static tests at	25
2	Static tests at	125
3	Static tests at	-55
4	Dynamic tests at	25
5	Dynamic tests at	125
6	Dynamic tests at	-55
7	Functional tests at	25
8A	Functional tests at	125
8B	Functional tests at	-55
9	Switching tests at	25
10	Switching tests at	125
11	Switching tests at	-55

LM101A 883 Electrical Characteristics

DC Parameters

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC} = \pm 20V, V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
V _{IO}	Input Offset Voltage	$V_{CM} = -15V, R_S = 50\Omega$		-2.0	2.0	mV	1
				-3.0	3.0	mV	2, 3
		$V_{CM} = 15V, R_S = 50\Omega$		-2.0	2.0	mV	1
				-3.0	3.0	mV	2, 3
		$R_{\rm S} = 50\Omega$		-2.0	2.0	mV	1
				-3.0	3.0	mV	2, 3
		$V_{\rm CC} = \pm 5 V, R_{\rm S} = 50 \Omega$		-2.0	2.0	mV	1
				-3.0	3.0	mV	2, 3
I _{IO}	Input Offset Current	V _{CM} = -15V		-10	10	nA	1
				-20	20	nA	2, 3
		$V_{CM} = 15V$		-10	10	nA	1
				-20	20	nA	2, 3
				-10	10	nA	1
				-20	20	nA	2, 3
		$V_{CC} = \pm 5V$		-10	10	nA	1
				-20	20	nA	2, 3
±I _{IB}	Input Bias Current	V _{CM} = -15V		1.0	75	nA	1
				1.0	100	nA	2, 3
		$V_{CM} = 15V$		1.0	75	nA	1
				1.0	100	nA	2, 3
				1.0	75	nA	1
				1.0	100	nA	2, 3
		$V_{\rm CC} = \pm 5 V$		1.0	75	nA	1
				1.0	100	nA	2, 3
PSRR+	Power Supply Rejection Ratio	+V _{CC} = +20V and +5V, -V _{CC} =-20V, R _S =50Ω		80		dB	1, 2, 3
PSRR-	Power Supply Rejection Ratio	+V _{CC} = +20V, -V _{CC} = -20V and -5V, R _S =50 Ω		80		dB	1, 2, 3
CMRR	Common Mode Rejection Ratio	$-15V \le V_{CM} \le 15V, R_S = 50\Omega$		80		dB	1, 2, 3

LM101A 883 Electrical Characteristics (Continued)

DC Parameters (Continued)

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC} = \pm 20V, V_{CM} = 0V$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
I _{cc}	Supply Current				3.0	mA	1
					2.5	mA	2
					3.5	mA	3
$+V_{IO}$ Adj	Input Offset Voltage Adjust			4.0		mV	1, 2, 3
–V _{IO} Adj	Input Offset Voltage Adjust				-4.0	mV	1, 2, 3
+l _{os}	Short Circuit Current			-45	-7.0	mA	1, 2, 3
-I _{os}	Short Circuit Current			7.0	45	mA	1, 2, 3
VI	Input Voltage Range	$V_{\rm CC} = \pm 20 V$	(Note 6)	-15	15	V	1, 2, 3
+A _{VS}	Large Signal Gain	$V_{CC} = \pm 15V, R_{S} = 0, R_{L} = 2K\Omega,$		50		V/mV	4
		V _O =10V		25		V/mV	5, 6
-A _{VS}	Large Signal Gain	$V_{CC} = \pm 15V, R_{S} = 0, R_{L} = 2K\Omega,$		50		V/mV	4
		V _O =-10V		25		V/mV	5, 6
R _I	Input Resistance		(Note 7)	1.5		MΩ	4
			(Note 7)	0.5		MΩ	5, 6
+V _{OP}	Output Voltage Swing	$R_L = 10K\Omega$		16		V	4, 5, 6
		$R_L = 2K\Omega$		15		V	4, 5, 6
		$R_L = 10K\Omega$, $V_{CC} = \pm 15V$		12		V	4, 5, 6
		$R_L = 2K\Omega, V_{CC} = \pm 15V$		10		V	4, 5, 6
-V _{OP}	Output Voltage Swing	$R_L = 10K\Omega$			-16	V	4, 5, 6
		$R_L = 2K\Omega$			-15	V	4, 5, 6
		$R_{L} = 10K\Omega, V_{CC} = \pm 15V$			-12	V	4, 5, 6
		$R_L = 2K\Omega, V_{CC} = \pm 15V$			-10	V	4, 5, 6

AC Parameters

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC} = \pm 20V, R_L = 2K\Omega, A_V = 1$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
+SR	Slew Rate	$V_1 = -5V$ to 5V			0.2	V/µS	7
-SR	Slew Rate	$V_{I} = 5V$ to $-5V$			0.2	V/µS	7
G _{BW}	Gain Bandwidth	$V_{I} = 50 m V_{RMS}$, f = 20KHz			0.25	MHz	7

LM101A QML & RH Electrical Characteristics (Note 10)

DC Parameters

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC}=\pm 20V, V_{CM}=0V, R_S=50\Omega$

Symbol	Parameter	Conditions	Notes	Min	Мах	Units	Sub- groups
V _{IO}	Input Offset Voltage	$+V_{CC} = 35V, -V_{CC} = -5V,$		-2.0	+2.0	mV	1
		V _{CM} = -15V		-3.0	+3.0	mV	2, 3
		$+V_{\rm CC} = 5V, -V_{\rm CC} = -35V,$		-2.0	+2.0	mV	1
		$V_{CM} = +15V$		-3.0	+3.0	mV	2, 3
		$V_{CM} = 0V$		-2.0	+2.0	mV	1
				-3.0	+3.0	mV	2, 3
		$+V_{\rm CC} = 5V, -V_{\rm CC} = -5V,$		-2.0	+2.0	mV	1
		$V_{CM} = 0V$		-3.0	+3.0	mV	2, 3
I _{IO}	Input Offset Current	$+V_{CC} = 35V, -V_{CC} = -5V,$		-10	+10	nA	1, 2
		$V_{CM} = -15V, R_{S} = 100K\Omega$		-20	+20	nA	3
		$+V_{\rm CC} = 5V, -V_{\rm CC} = -35V,$		-10	+10	nA	1, 2
		$V_{CM} = +15V, R_{S} = 100K\Omega$		-20	+20	nA	3
		$V_{CM} = 0V, R_S = 100K\Omega$		-10	+10	nA	1, 2
				-20	+20	nA	3
		$+V_{\rm CC} = 5V, -V_{\rm CC} = -5V,$		-10	+10	nA	1, 2
		$V_{CM} = 0V, R_S = 100K\Omega$		-20	+20	nA	3
±l _{IB}	Input Bias Current	$+V_{\rm CC} = 35V, -V_{\rm CC} = -5V,$		-0.1	75	nA	1, 2
		$V_{CM} = -15V, R_{S} = 100K\Omega$		-0.1	100	nA	3
		$+V_{\rm CC} = 5V, -V_{\rm CC} = -35V,$		-0.1	75	nA	1, 2
		V_{CM} = +15V, R_{S} = 100K Ω		-0.1	100	nA	3
		$V_{CM} = 0V, R_S = 100K\Omega$		-0.1	75	nA	1, 2
				-0.1	100	nA	3
		$+V_{\rm CC} = 5V, -V_{\rm CC} = -5V,$		-0.1	75	nA	1, 2
		$V_{CM} = 0V, R_S = 100K\Omega$		-0.1	100	nA	3
+PSRR	Power Supply Rejection Ratio	$+V_{CC} = 10V, -V_{CC} = -20V$		-50	+50	μV/V	1
				-100	+100	μV/V	2, 3
-PSRR	Power Supply Rejection Ratio	$+V_{CC} = 20V, -V_{CC} = -10V$		-50	+50	μV/V	1
				-100	+100	μV/V	2, 3
CMRR	Common Mode Rejection Ratio	$V_{CC} = \pm 35V$ to $\pm 5V$, $V_{CM} = \pm 15V$		80		dB	1, 2, 3
+V _{IO} Adj	Adjustment for Input Offset Voltage			4.0		mV	1, 2, 3
-V _{IO} Adj	Adjustment for Input Offset Voltage				-4.0	mV	1, 2, 3
+I _{OS}	Output Short Circuit Current	$\begin{split} + V_{CC} &= 15 V, \ \text{-}V_{CC} = \text{-}15 V, \\ t &\leq 25 \text{mS}, \ V_{CM} = \text{-}15 V \end{split}$		-60		mA	1, 2, 3
-I _{os}	Output Short Circuit Current	$\begin{split} + V_{\rm CC} &= 15 \text{V}, \ \text{-}V_{\rm CC} = \text{-}15 \text{V}, \\ t &\leq 25 \text{mS}, \ \text{V}_{\rm CM} = \text{+}15 \text{V} \end{split}$			+60	mA	1, 2, 3
I _{CC}	Power Supply Current	$+V_{CC} = 15V, -V_{CC} = -15V$			3.0	mA	1
					2.32	mA	2
					3.5	mA	3
$\Delta V_{IO} / \Delta T$	Temperature Coefficient of	$-55^{\circ}C \le T_A \le +25^{\circ}C$	(Note 8)	-18	+18	µV/°C	2
	Input Offset Voltage	$+25^{\circ}C \leq T_A \leq +125^{\circ}C$	(Note 8)	-15	+15	uV/°C	3
Δ I _{IO} / Δ T	Temperature Coefficient of	$-55^{\circ}C \le T_A \le +25^{\circ}C$	(Note 8)	-200	+200	pA/°C	2
	Input Offset Current	$+25^{\circ}C \le T_A \le +125^{\circ}C$	(Note 8)	-100	+100	pA/°C	3

LM101A QML & RH Electrical Characteristics (Note 10) (Continued)

DC Parameters (Continued)

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC} = \pm 20V, V_{CM} = 0V, R_S = 50\Omega$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
-A _{VS}	Large Signal (Open Loop)	$R_L = 2K\Omega, V_O = -15V$	(Note 9)	50		V/mV	4
	Voltage Gain		(Note 9)	25		V/mV	5, 6
		$R_{L} = 10K\Omega, V_{O} = -15V$	(Note 9)	50		V/mV	4
			(Note 9)	25		V/mV	5, 6
+A _{VS}	Large Signal (Open Loop)	$R_L = 2K\Omega, V_O = +15V$	(Note 9)	50		V/mV	4
	Voltage Gain		(Note 9)	25		V/mV	5, 6
		$R_{L} = 10K\Omega, V_{O} = +15V$	(Note 9)	50		V/mV	4
			(Note 9)	25		V/mV	5, 6
A _{VS}	Large Signal (Open Loop) Voltage Gain	$V_{CC} = \pm 5V, R_L = 2K\Omega,$ $V_O = \pm 2V$	(Note 9)	10		V/mV	4,5, 6
		$V_{CC} = \pm 5V, R_L = 10K\Omega,$ $V_O = \pm 2V$	(Note 9)	10		V/mV	4,5, 6
+V _{OP}	Output Voltage Swing	$R_{L} = 10K\Omega, V_{CM} = -20V$		+16		V	4,5, 6
		$RL = 2K\Omega$, $V_{CM} = -20V$		+15		V	4,5, 6
-V _{OP}	Output Voltage Swing	$R_{L} = 10K\Omega, V_{CM} = 20V$			-16	V	4,5, 6
		$R_L = 2K\Omega, V_{CM} = 20V$			-15	V	4,5, 6

AC Parameters

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC} = \pm 20V, V_{CM} = 0V, R_{S} = 50\Omega$

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub-	
						max	Onito	groups
+SR	Slew Rate	$A_{V} = 1, V_{I} = -5V \text{ to } +5V$		0.3		V/µS	7, 8A	
				0.2		V/µS	8B	
-SR	Slew Rate	$A_V = 1, V_I = +5V \text{ to } -5V$		0.3		V/µS	7, 8A	
				0.2		V/µS	8B	
TR _{TR}	Rise Time	$A_V = 1, V_I = 50mV$			800	nS	7, 8A, 8B	
TR _{os}	Overshoot	$A_V = 1, V_I = 50mV$			25	%	7	
					35	%	8A, 8B	
NI _{BB}	Noise Broadband	BW = 10Hz to 5KHz, $R_s = 0\Omega$			15	μV _{RMS}	7	
NI _{PC}	Noise Popcorn	BW = 10Hz to 5KHz,			00		7	
		R _S = 100KΩ			00	^µ v _{PK}	'	

DC Parameters Drift Values

The following conditions apply to all parameters, unless otherwise specified

 $V_{CC}=\pm20V,\,V_{CM}=0V,\,R_S=50\Omega$

Delta calculations performed on QMLV devices at group B, Subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Units	Sub- groups
V _{IO}	Input Offset Voltage	$V_{CM} = 0V$		-0.5	0.5	mV	1
± I _{IB}	Input Bias Current	$V_{CM} = 0V, R_S = 100K\Omega$		-7.5	7.5	nA	1

Notes

Note 2: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating ratings indicate conditions for which the device is intended to be functional, but do no guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: For supply voltages less than $\pm 15V$, the absolute maximum input voltage is equal to the supply voltage.

Note 4: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{Jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{Dmax} = (T_{Jmax} - T_A) / \theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower.

Note 5: Human body model, 100 pF discharged through 1.5 k $\Omega.$

Note 6: Parameter guaranteed by the input conditions of several DC parameters

Note 7: Parameter guaranteed, not tested.

Note 8: Calculated parameter

Note 9: Datalog reading of K = V/mV.

Note 10: Pre and post irradiation limits are identical to those listed under AC and DC electrical characteristics. These parts may be dose rate sensitive in a space environment and demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in Mil-Std-883, Method 1019

Note 11: Pin connections shown are for 8-pin packages.







Typical Performance Characteristics LM101A (Continued)





Typical Performance Characteristics for Various Compensation Circuits (Note 11)











C_S= 30 pF C2 = 10 C1

















Application Hints (Note 11)



Although the LM101A is designed for trouble free operation, experience has indicated that it is wise to observe certain precautions given below to protect the devices from abnormal operating conditions. It might be pointed out that the advice given here is applicable to practically any IC op amp, although the exact reason why may differ with different devices.

When driving either input from a low-impedance source, a limiting resistor should be placed in series with the input lead to limit the peak instantaneous output current of the source to something less than 100 mA. This is especially important when the inputs go outside a piece of equipment where they could accidentally be connected to high voltage sources. Large capacitors on the input (greater than 0.1 μF) should be treated as a low source impedance and isolated with a resistor. Low impedance sources do not cause a problem unless their output voltage exceeds the supply voltage. However, the supplies go to zero when they are turned off, so the isolation is usually needed.

The output circuitry is protected against damage from shorts to ground. However, when the amplifier output is connected to a test point, it should be isolated by a limiting resistor, as test points frequently get shorted to bad places. Further, when the amplifer drives a load external to the equipment, it is also advisable to use some sort of limiting resistance to preclude mishaps.

Precautions should be taken to insure that the power supplies for the integrated circuit never become reversed—even under transient conditions. With reverse voltages greater than 1V, the IC will conduct excessive current, fusing internal aluminum interconnects. If there is a possibility of this happening, clamp diodes with a high peak current rating should be installed on the supply lines. Reversal of the voltage between V⁺ and V⁻ will always cause a problem, although reversals with respect to ground may also give difficulties in many circuits.

The minimum values given for the frequency compensation capacitor are stable only for source resistances less than 10 k Ω , stray capacitances on the summing junction less than 5 pF and capacitive loads smaller than 100 pF. If any of these conditions are not met, it becomes necessary to overcompensate the amplifier with a larger compensation capacitor. Alternately, lead capacitors can be used in the feedback network to negate the effect of stray capacitance and large feedback resistors or an RC network can be added to isolate capacitive loads.

Although the LM101A is relatively unaffected by supply bypassing, this cannot be ignored altogether. Generally it is necessary to bypass the supplies to ground at least once on every circuit card, and more bypass points may be required if more than five amplifiers are used. When feed-forward compensation is employed, however, it is advisable to bypass the supply leads of each amplifier with low inductance capacitors because of the higher frequencies involved.



Typical Applications (Note 11)







Typical Applications (Note 11) (Continued) Low Frequency Square Wave Generator R1 1M

LOW IMPEDANCE OUTPUT C1 2 R4 5K CLAMPED OUTPUT 6 LM301A I **R**3 10M D1 3 6.2V R2 D2 1M 6.2V 20122336

Low Drift Sample and Hold



Voltage Comparator for Driving DTL or TTL Integrated Circuits



*Polycarbonate-dielectric capacitor

LM101AQML

20122338

Revision History Section									
Date Released	Revision	Section	Originator	Changes					
01/05/06	A	New Release to corporate format	L. Lytle	2 MDS datasheets converted into one Corp. datasheet format. MNLM101A-X Rev 0A0 and MRLM101A-X-RH rev 1C2 MDS datasheets will be archived.					



